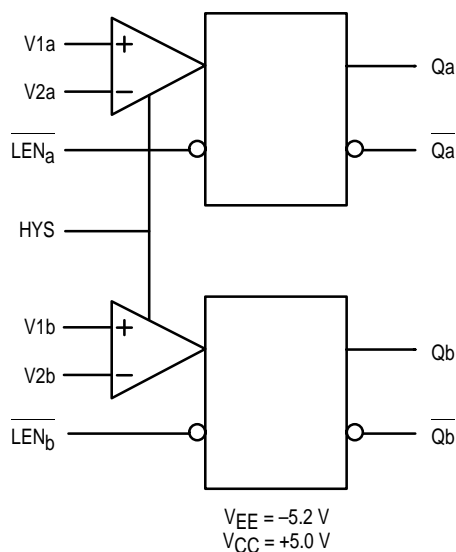"MC10E1652FNR2G"

Dual ECL Output Comparator With Latch

The MC10E1652 is functionally and pin-for-pin compatible with the MC10E1651 and thus the MC1651 in the MECL III™ family, but is fabricated using Motorola's advanced MOSAIC III™ process and is output compatible with 10H logic devices. In addition, the device is available in both a 16-pin DIP and a 20-pin surface mount package. However, the MC10E1652 provides user programmable hysteresis.

The latch enable ($\overline{LEN_a}$ and $\overline{LEN_b}$) input pins operate from standard ECL 10H™ logic levels. When the latch enable is at a logic high level the MC10E1652 acts as a comparator, hence Q will be at a logic high level if V1 > V2 (V1 is more positive than V2). $\overline{Q}$ is the complement of Q. When the latch enable input goes to a low logic level, the outputs are latched in their present state, providing the latch enable setup and hold time constraints are met. The level of input hysteresis is controlled by applying a bias voltage to the HYS pin.
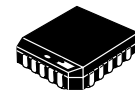
- Typical 3.0 dB Bandwidth > 1.0 GHz
- Typical V to Q Propagation Delay of 775 ps
- Typical Output Rise/Fall of 350 ps
- Common Mode Range –2.0 V to +3.0 V
- Individual Latch Enables
- Differential Outputs
- Programmable Input Hysteresis

MC10E1652

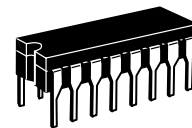### DUAL ECL OUTPUT COMPARATOR WITH LATCH

FN SUFFIX
PLASTIC PACKAGE
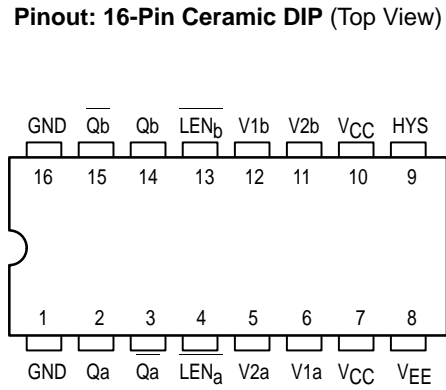CASE 775-02

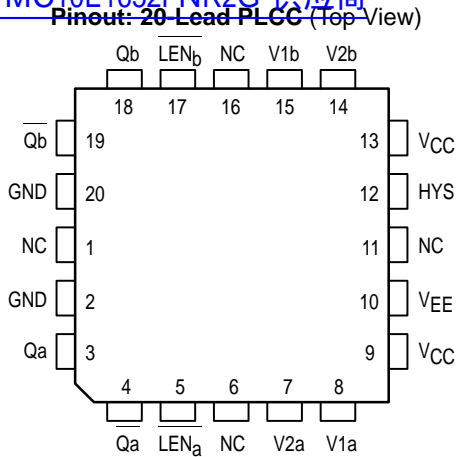**L SUFFIX**
CERAMIC PACKAGE
CASE 620-10

LOGIC DIAGRAM

$V_{EE} = -5.2$ V
$V_{CC} = +5.0$ V

FUNCTION TABLE

$\overline{LEN}$	V1, V2	Function
H	V1 > V2	H
H	V1 < V2	L
L	X	Latched

REV 1

MOTOROLA

MC10E1652

Pinout: 20-Lead PLCC (Top View)

```
          Qb  LENb  NC  V1b  V2b
          18   17   16   15   14

  Qb   19                          13   VCC
  GND  20                          12   HYS
  NC    1                          11   NC
  GND   2                          10   VEE
  Qa    3                           9   VCC
          4    5    6    7    8

          Qa  LENa  NC  V2a  V1a
```

Pinout: 16-Pin Ceramic DIP (Top View)

```
   GND   Qb   Qb  LENb  V1b  V2b  VCC  HYS
   16    15   14   13   12   11   10    9


    1     2    3    4    5    6    7    8
   GND   Qa   Qa  LENa  V2a  V1a  VCC  VEE
```

ABSOLUTE MAXIMUM RATINGS (Beyond which device life may be impaired)

Symbol	Characteristic	Min	Typ	Max	Unit
VSUP	Total Supply Voltage $|V_{EE}| + |V_{CC}|$			12.0	V
VPP	Differential Input Voltage $|V1 - V2|$			3.7	V

DC CHARACTERISTICS (V_{EE} = −5.2 V ±5%; V_{CC} = +5.0 V ±5%)

Symbol	Characteristic	0°C Min	0°C Typ	0°C Max	25°C Min	25°C Typ	25°C Max	85°C Min	85°C Typ	85°C Max	Unit	Condition
V_{OH}	Output HIGH Voltage	−1020		−840	−980		−810	−920		−735	mV	
V_{OL}	Output Low Voltage	−1950		−1630	−1950		−1630	−1950		−1600	mV	
II, I_{IH}	Input Current (V1, V2) / Input HIGH Current (LEN)			65 / 150			65 / 150			65 / 150	µA	
I_{CC}, I_{EE}	Positive Supply Current / Negative Supply Current			50 / −55			50 / −55			50 / −55	mA	
VCMR	Common Mode Range	−2.0		3.0	−2.0		3.0	−2.0		3.0	V	
Hys	Hysteresis		27			27			30		mV	1
V_{skew}	Hysteresis Skew		−1.0			−1.0			0		mV	2
C_{in}	Input Capacitance DIP / PLCC			3 / 2			3 / 2			3 / 2	pF	

1. The HYS pin programming characterization information is shown in Figure 2, The hysteresis values indicated in the data sheet are for the condition in which the voltage on the HYS pin is set to V_{EE}.
2. Hysteresis skew (V_{skew}) is provided to indicate the offset of the hysteresis window. For example, at 25°C the nominal hysteresis value is 27 mV and the V_{skew} value indicates that the hysteresis was skewed from the reference level by 1 mV in the negative direction. Hence the hysteresis window ranged from 14 mV below the reference level to 13 mV above the reference level. All hysteresis measurements were determined using a reference voltage of 0 mV. The hysteresis skew values apply over the programming range shown in Figure 2.
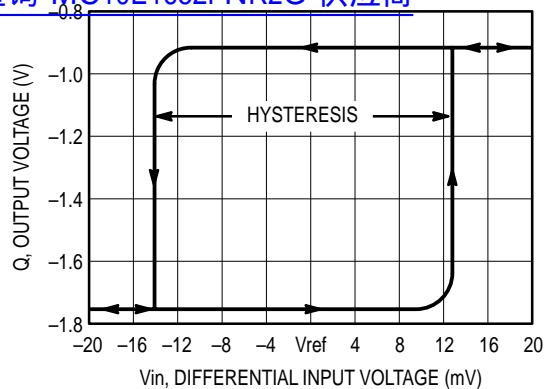
Figure 1. Typical Hysteresis Curve

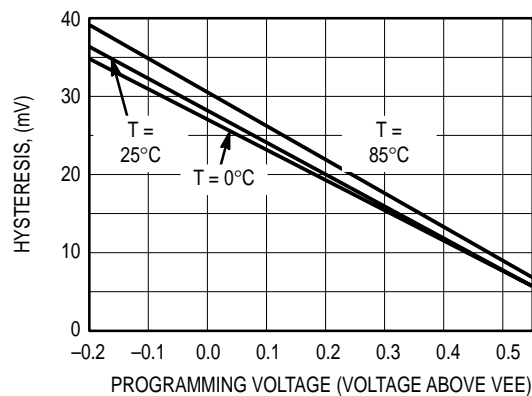Figure 2. Hysteresis Programming Voltage

AC CHARACTERISTICS

(V_{EE} = −5.2 V ±5%; V_{CC} = +5.0 V ±5%)

Symbol	Characteristic	0°C			25°C			85°C			Unit	Condition
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
t_{PLH} t_{PHL}	Propagation Delay to Output V to Q LEN to Q	600 400	750 575	900 750	625 400	775 575	925 750	700 500	850 650	1050 850	ps	1
t_S	Setup Time V	450	300		450	300		550	350		ps	
t_h	Enable Hold Time V	−50	−250		−50	−250		−100	−250		ps	
t_{pw}	Minimum Pulse Width LEN	400			400			400			ps	
t_{skew}	Within Device Skew		15			15			15		ps	2
T_{DE}	Delay Dispersion (ECL Levels)					100 60					ps	3, 4 3, 5
T_{DL}	Delay Dispersion (TTL Levels)					350 100					ps	6, 7 5, 6
t_r t_f	Rise/Fall Times 20-80%	225	325	475	225	325	475	250	375	500	ps	

1. The propagation delay is measured from the crosspoint of the input signal and the threshold value to the crosspoint of the Q and $\overline{Q}$ output signals. For propagation delay measurements the threshold level (V_{THR}) is centered about an 850 mV input logic swing with a slew rate of 0.75 V/NS. There is an insignificant change in the propagation delay over the input common mode range.
2. t_{skew} is the propagation delay skew between comparator A and comparator B for a particular part under identical input conditions.
3. Refer to Figure 4 and note that the input is at 850 mV ECL levels with the input threshold range between the 20% and 80% points. The delay is measured from the crosspoint of the input signal and the threshold value to the crosspoint of the Q and $\overline{Q}$ output signals.
4. The slew rate is 0.25 V/NS for input rising edges.
5. The slew rate is 0.75 V/NS for input rising edges.
6. Refer to Figure 5 and note that the input is at 2.5 V TTL levels with the input threshold range between the 20% and 80% points. The delay is measured from the crosspoint of the input signal and the threshold value to the crosspoint of the Q and $\overline{Q}$ output signals.
7. The slew rate is 0.3 V/NS for input rising edges.

APPLICATIONS INFORMATION

The timing diagram (Figure 3) is presented to illustrate the MC10E1652's compare and latch features. When the signal on the LEN pin is at a logic high level, the device is operating in the "compare mode," and the signal on the input arrives at the output after a nominal propagation delay (t_{PHL}, t_{PLH}). The input signal must be asserted for a time, t_S, prior to the

negative going transition on $\overline{LEN}$ and held for a time, t_h, after the LEN transition. After time t_h, the latch is operating in the "latch mode," thus transitions on the input do not appear at the output. The device continues to operate in the "latch mode" until the latch is asserted once again. Moreover, the LEN pulse must meet the minimum pulse width (t_{pw})

requirement to effect the correct input output relationship. Note that the LEN waveform in Figure 3 shows the LEN signal swinging around a reference labeled $V_{BB_{INT}}$, this waveform emphasizes the requirement that LEN follow typical ECL 10KH logic levels because VBB_{INT} is the internally generated reference level, hence is nominally at the ECL VBB level.

Finally, V_{OD} is the input voltage overdrive and represents the voltage level beyond the threshold level (V_{THR}) to which the input is driven. As an example, if the threshold level is set on one of the comparator inputs as 80 mV and the input signal swing on the complementary input is from zero to 100 mV, the positive going overdrive would be 20 mV and the negative going overdrive would be 80 mV. The result of differing overdrive levels is that the devices have shorter propagation delays with greater overdrive because the threshold level is crossed sooner than the case of lower overdrive levels. Typically, semiconductor manufactures refer to the threshold voltage as the input offset voltage (VOS) since the threshold voltage is the sum of the externally supplied reference voltage and inherent device offset voltage.
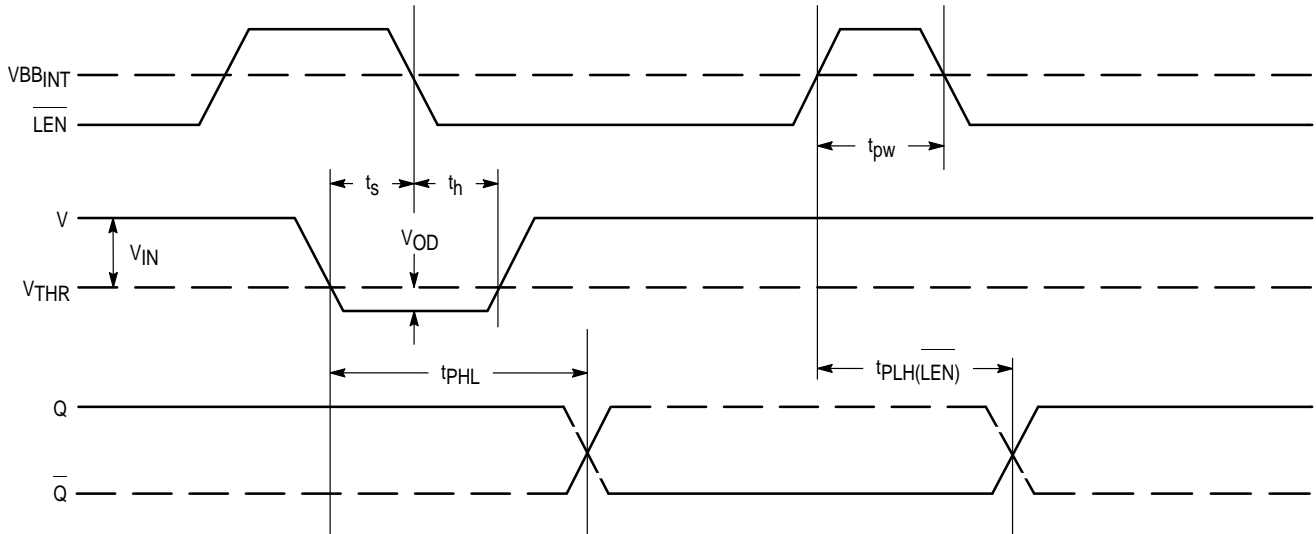
Figure 3. Input/Output Timing Diagram

DELAY DISPERSION

Under a constant set of input conditions comparators have a specified nominal propagation delay. However, since propagation delay is a function of input slew rate and input voltage overdrive the delay dispersion parameters, T_{DE} and T_{DT}, are provided to allow the user to adjust for these variables (where T_{DE} and T_{DT} apply to inputs with standard ECL and TTL levels, respectively).

Figure 4 and Figure 5 define a range of input conditions which incorporate varying input slew rates and input voltage overdrive. For input parameters that adhere to these constraints the propagation delay can be described as:

$$T_{NOM} \pm T_{DE} \text{ (or } T_{DT})$$

where T_{NOM} is the nominal propagation delay. T_{NOM} accounts for nonuniformity introduced by temperature and voltage variability, whereas the delay dispersion parameter takes into consideration input slew rate and input voltage overdrive variability. Thus a modified propagation delay can be approximated to account for the effects of input conditions that differ from those under which the parts where tested. For example, an application may specify an ECL input with a slew rate of 0.25 V/NS, an overdrive of 17 mV and a temperature of 25°C, the delay dispersion parameter would be 100 ps. The modified propagation delay would be
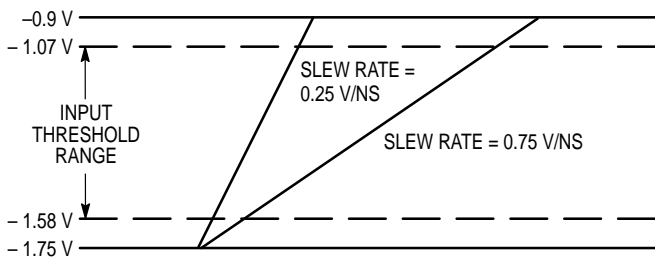
$$775ps \pm 100ps$$
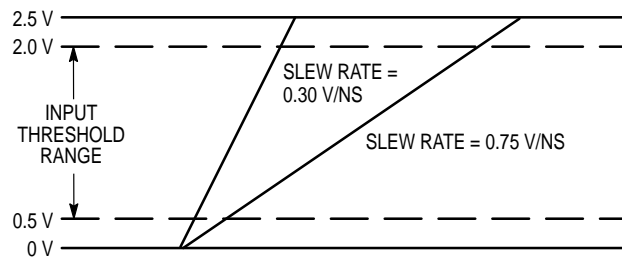

Figure 4. ECL Dispersion Test Input Conditions

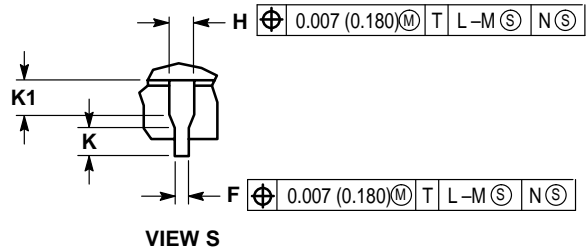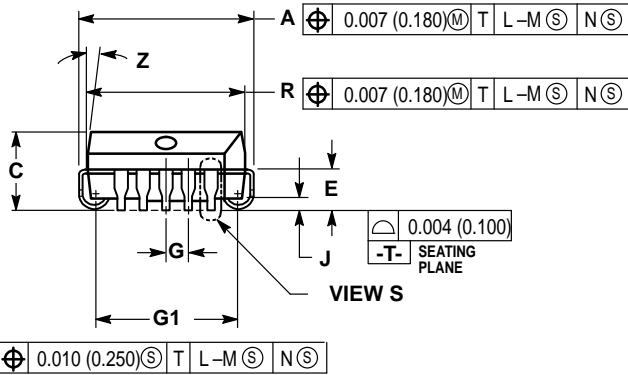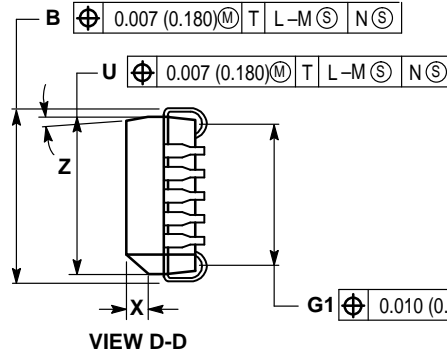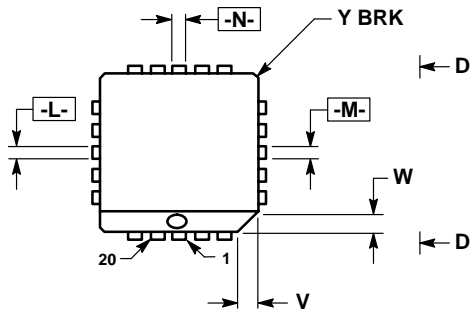**Figure 5. TTL Dispersion Test Input Conditions**

"MC10E1652FNR2G"

OUTLINE DIMENSIONS

FN SUFFIX
PLASTIC PLCC PACKAGE
CASE 775–02
ISSUE C


VIEW D-D

VIEW S

VIEW S

NOTES:
1. DATUMS -L-, -M-, AND -N- DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.
2. DIM G1, TRUE POSITION TO BE MEASURED AT DATUM -T-, SEATING PLANE.
3. DIM R AND U DO NOT INCLUDE MOLD FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
5. CONTROLLING DIMENSION: INCH.
6. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300). DIMENSIONS R AND U ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
7. DIMENSION H DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.385	0.395	9.78	10.03
B	0.385	0.395	9.78	10.03
C	0.165	0.180	4.20	4.57
E	0.090	0.110	2.29	2.79
F	0.013	0.019	0.33	0.48
G	0.050 BSC		1.27 BSC	
H	0.026	0.032	0.66	0.81
J	0.020	—	0.51	—
K	0.025	—	0.64	—
R	0.350	0.356	8.89	9.04
U	0.350	0.356	8.89	9.04
V	0.042	0.048	1.07	1.21
W	0.042	0.048	1.07	1.21
X	0.042	0.056	1.07	1.42
Y	—	0.020	—	0.50
Z	2°	10°	2°	10°
G1	0.310	0.330	7.88	8.38
K1	0.040	—	1.02	—

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MC10E1652

OUTLINE DIMENSIONS

L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V
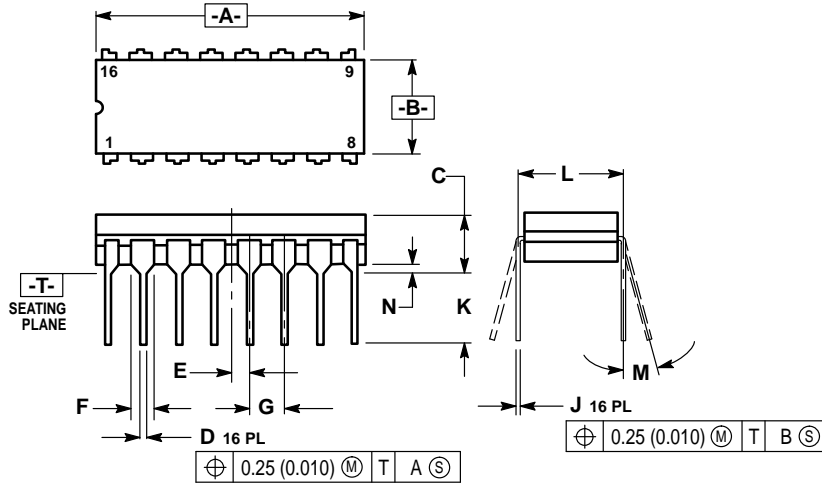
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

"MC10E1652FNR2G"

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MC10E1652/D